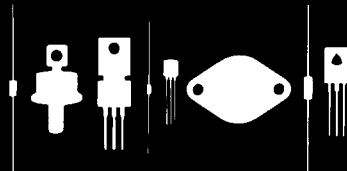


Central
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145 Adams Avenue
Hauppauge, New York 11788



2N3819

N-CHANNEL SILICON JUNCTION FET

JEDEC TO-92 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3819 type is a Silicon N-Channel Junction Field Effect Transistor designed for RF Amplifier and mixer applications.

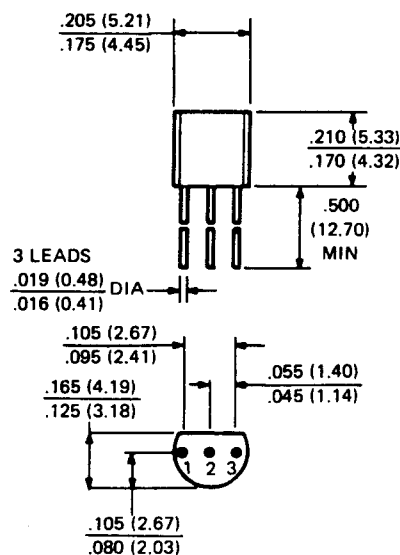
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNIT
Drain-Gate Voltage	V_{GD}	25	V
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage (Reverse)	V_{GS}	25	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	360	mW
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_{DSS}	$V_{DS}=15\text{V}$	2	20	mA
I_{GSS}	$V_{GS}=15\text{V}$		2.0	nA
I_{GSS}	$V_{GS}=15\text{V}, T_A=100^{\circ}\text{C}$		2.0	μA
BV_{GSS}	$I_G=1.0\mu\text{A}$	25		V
V_{GS}	$V_{DS}=15\text{V}, I_D=200\mu\text{A}$	0.5	7.5	V
$V_{GS(OFF)}$	$V_{DS}=15\text{V}, I_D=2.0\text{nA}$		8.0	V
C_{iss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		8.0	pF
C_{rss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		4.0	pF
f_{yfs1}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$	2000	6500	μmho
f_{yfs1}	$V_{DS}=15\text{V}, V_{GS}=0, f=100\text{MHz}$	1600		μmho
f_{yos1}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}$		50	μmho

OUTLINE DRAWING:



LEAD CODE:

1. DRAIN
2. GATE
3. SOURCE

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